



BUK7613-100E

N-channel TrenchMOS standard level FET

5 October 2012

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

1.2 Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with VGS(th) rating of greater than 1V at 175 °C

1.3 Applications

- 12V, 24V and 48V Automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

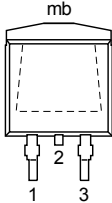
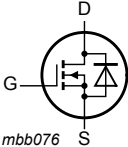
1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$	-	-	100	V
I_D	drain current	$V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}; \text{Fig. 1}$	-	-	72	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ °C}; \text{Fig. 2}$	-	-	182	W
Static characteristics						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}; I_D = 20\text{ A}; T_j = 25\text{ °C}; \text{Fig. 11}$	-	10.2	13	mΩ
Dynamic characteristics						
Q_{GD}	gate-drain charge	$V_{GS} = 10\text{ V}; I_D = 20\text{ A}; V_{DS} = 80\text{ V}; T_j = 25\text{ °C}; \text{Fig. 13}; \text{Fig. 14}$	-	25.4	35.6	nC

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	 D2PAK (SOT404)	 mbb076
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
BUK7613-100E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404

4. Marking

Table 4. Marking codes

Type number	Marking code
BUK7613-100E	BUK7613-100E

5. Limiting values

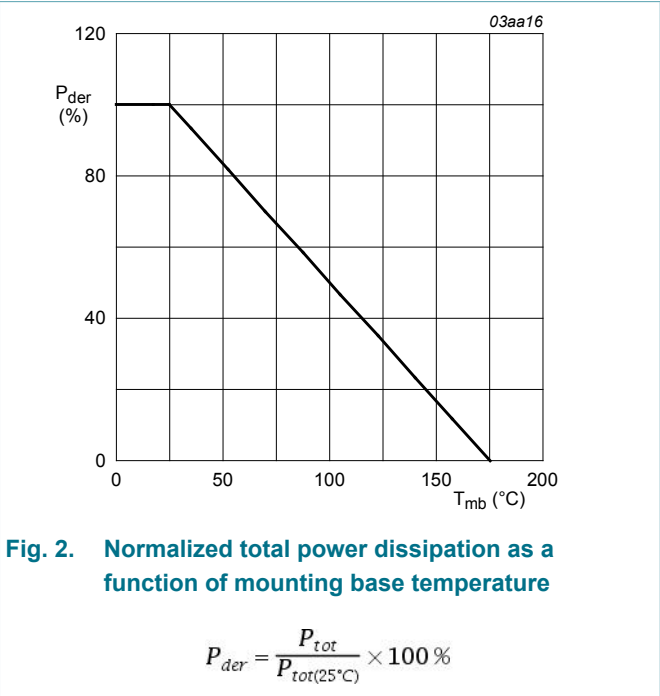
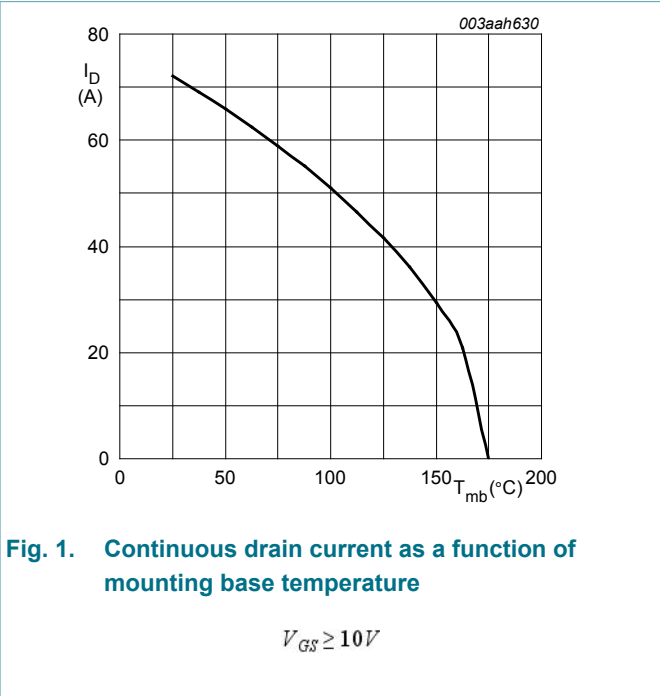
Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage	$T_j \geq 25\text{ }^{\circ}\text{C}$; $T_j \leq 175\text{ }^{\circ}\text{C}$	-	100	V
V_{DGR}	drain-gate voltage	$R_{GS} = 20\text{ k}\Omega$	-	100	V
V_{GS}	gate-source voltage	$T_j \leq 175\text{ }^{\circ}\text{C}$; DC	-20	20	V
I_D	drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 1	-	72	A
		$T_{mb} = 100\text{ }^{\circ}\text{C}$; $V_{GS} = 10\text{ V}$; Fig. 1	-	51	A
I_{DM}	peak drain current	$T_{mb} = 25\text{ }^{\circ}\text{C}$; pulsed; $t_p \leq 10\text{ }\mu\text{s}$; Fig. 4	-	288	A
P_{tot}	total power dissipation	$T_{mb} = 25\text{ }^{\circ}\text{C}$; Fig. 2	-	182	W
T_{stg}	storage temperature		-55	175	$^{\circ}\text{C}$
T_j	junction temperature		-55	175	$^{\circ}\text{C}$

Symbol	Parameter	Conditions		Min	Max	Unit
Source-drain diode						
I _S	source current	T _{mb} = 25 °C		-	72	A
I _{SM}	peak source current	pulsed; t _p ≤ 10 µs; T _{mb} = 25 °C		-	288	A
Avalanche ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I _D = 72 A; V _{sup} ≤ 100 V; R _{GS} = 50 Ω; V _{GS} = 10 V; T _{j(init)} = 25 °C; unclamped; Fig. 3	[1] [2]	-	121	mJ

- [1] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.
- [2] Refer to application note AN10273 for further information.



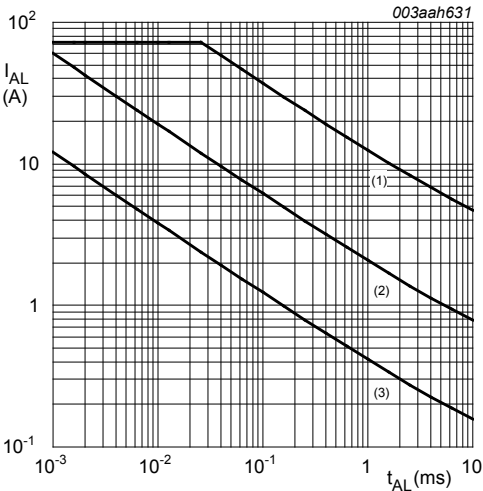


Fig. 3. Avalanche rating; avalanche current as a function of avalanche time

(1) $T_{j\ (init)} = 25^{\circ}C$; (2) $T_{j\ (init)} = 150^{\circ}C$; (3) Repetitive Avalanche

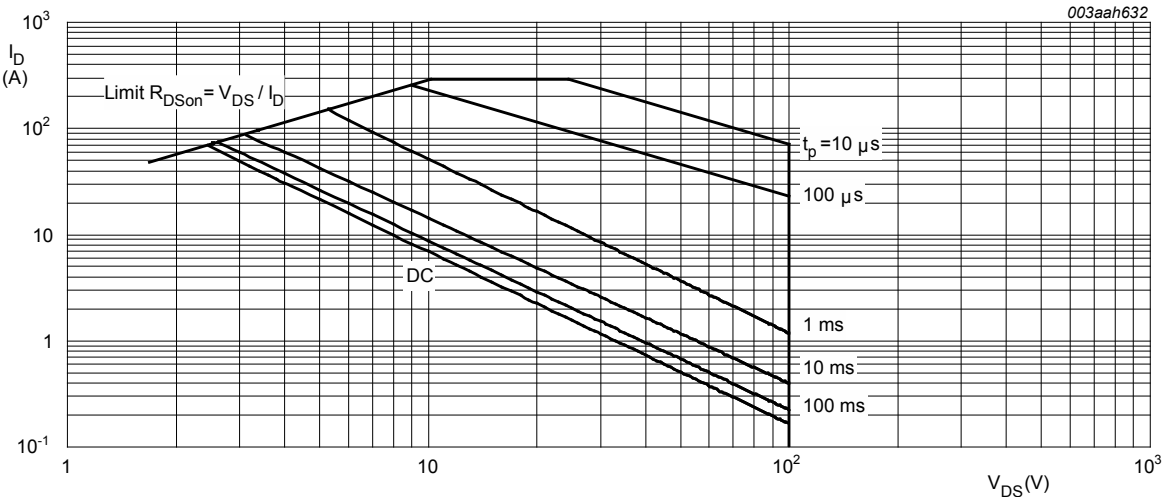


Fig. 4. Safe operating area; continuous and peak drain currents as a function of drain-source voltage

$T_{mb} = 25^{\circ}C$; I_{DM} is a single pulse

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	Fig. 5	-	-	0.82	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

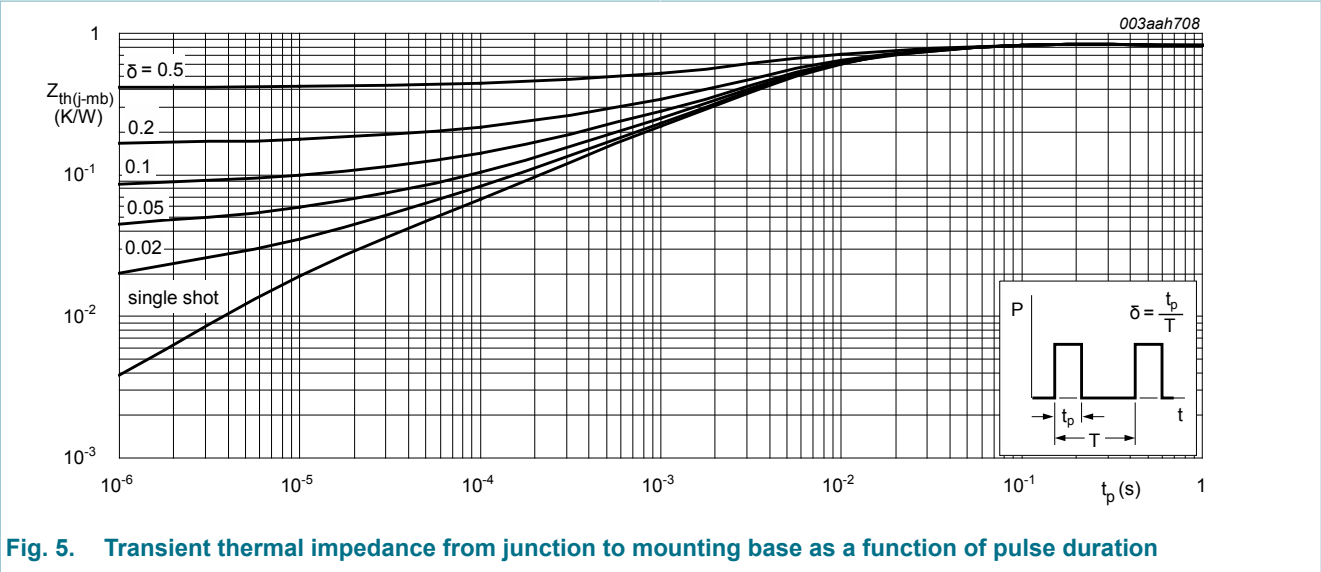


Fig. 5. Transient thermal impedance from junction to mounting base as a function of pulse duration

7. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Static characteristics						
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 250 μA; V _{GS} = 0 V; T _J = 25 °C	100	-	-	V
		I _D = 250 μA; V _{GS} = 0 V; T _J = -55 °C	90	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = 175 °C; Fig. 9	1	-	-	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _J = -55 °C; Fig. 9	-	-	4.5	V
I _{DSS}	drain leakage current	V _{DS} = 100 V; V _{GS} = 0 V; T _J = 25 °C	-	0.06	1	μA
		V _{DS} = 100 V; V _{GS} = 0 V; T _J = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _J = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _J = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 20 A; T _J = 25 °C; Fig. 11	-	10.2	13	mΩ
		V _{GS} = 10 V; I _D = 20 A; T _J = 175 °C; Fig. 11; Fig. 12	-	-	35.1	mΩ
R _G	gate resistance	f = 1 MHz	0.48	0.96	1.92	Ω
Dynamic characteristics						
Q _{G(tot)}	total gate charge	I _D = 20 A; V _{DS} = 80 V; V _{GS} = 10 V; T _J = 25 °C; Fig. 13; Fig. 14	-	69.4	97.2	nC
Q _{GS}	gate-source charge		-	15.5	21.7	nC

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Q_{GD}	gate-drain charge			-	25.4	35.6	nC
C_{iss}	input capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 20\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 15		-	3400	4533	pF
C_{oss}	output capacitance	$V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$; $f = 1\text{ MHz}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 15		-	327	392	pF
C_{rss}	reverse transfer capacitance			-	225	308	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 80\text{ V}$; $R_L = 4\text{ }\Omega$; $V_{GS} = 10\text{ V}$; $R_{G(ext)} = 5\text{ }\Omega$		-	17.5	26.3	ns
t_r	rise time			-	34	51	ns
$t_{d(off)}$	turn-off delay time			-	44.8	67.2	ns
t_f	fall time			-	34.1	51.2	ns
L_D	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nH
L_S	internal source inductance	measured from source lead to source bond pad ; $T_j = 25\text{ }^{\circ}\text{C}$		-	7.5	-	nH
Source-drain diode							
V_{SD}	source-drain voltage	$I_S = 20\text{ A}$; $V_{GS} = 0\text{ V}$; $T_j = 25\text{ }^{\circ}\text{C}$; Fig. 16		-	0.83	1.2	V
t_{rr}	reverse recovery time	$I_S = 20\text{ A}$; $dI_S/dt = -100\text{ A}/\mu\text{s}$; $V_{GS} = 0\text{ V}$; $V_{DS} = 25\text{ V}$		-	48.8	63.4	ns
Q_r	recovered charge			-	106	137.8	nC

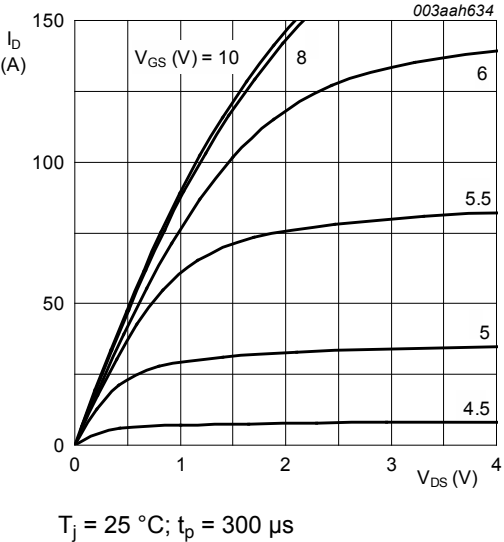


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

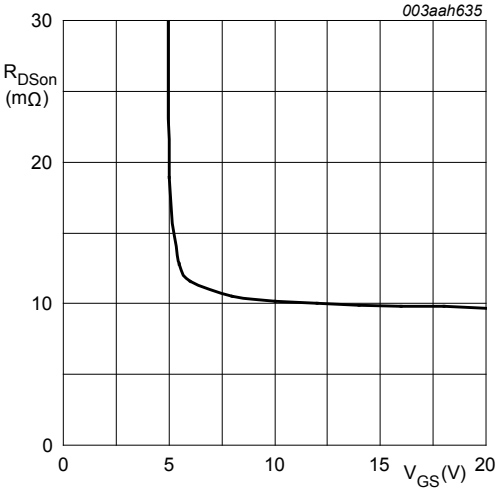


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$T_j = 25\text{ }^{\circ}\text{C}$; $I_D = 20\text{ A}$

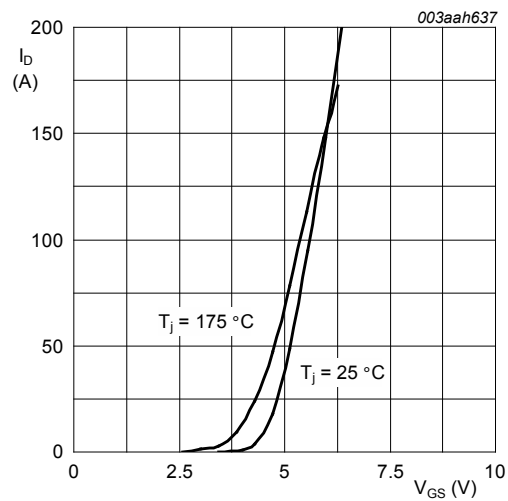


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values

$V_{DS} = 10\text{ V}$

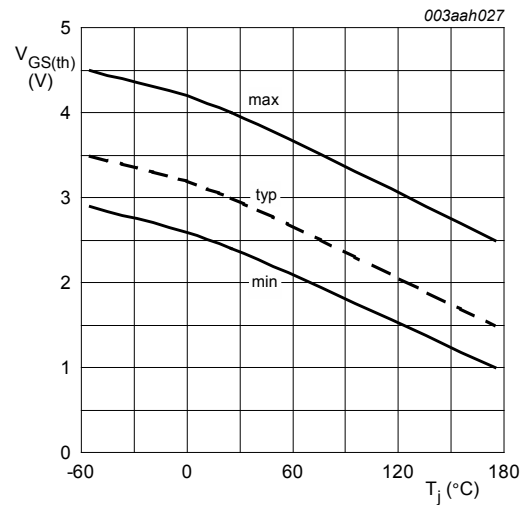


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$I_D = 1\text{ mA}; V_{DS} = V_{GS}$

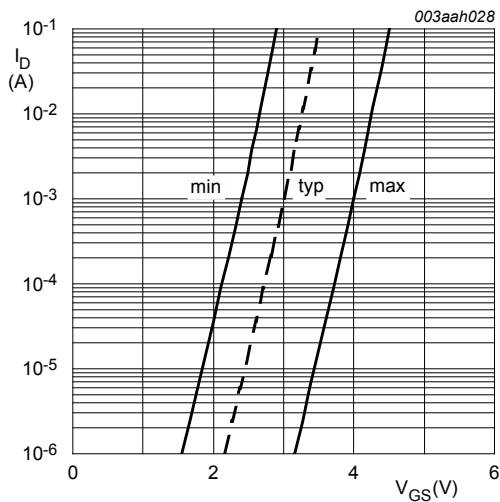


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$T_j = 25\text{ }^{\circ}\text{C}; V_{DS} = 5\text{ V}$

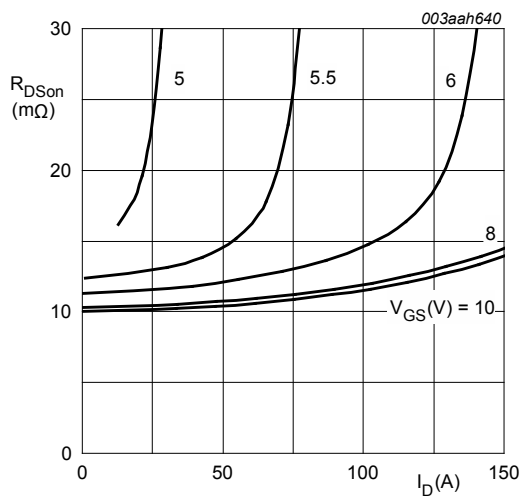


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

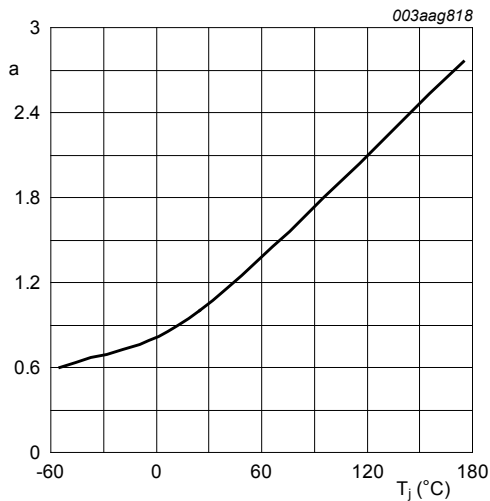


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25\text{ }^{\circ}\text{C})}}$$

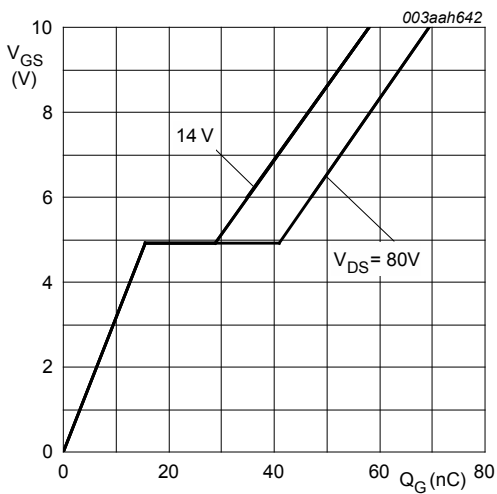


Fig. 13. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25\text{ }^{\circ}\text{C}; I_D = 20\text{ A}$$

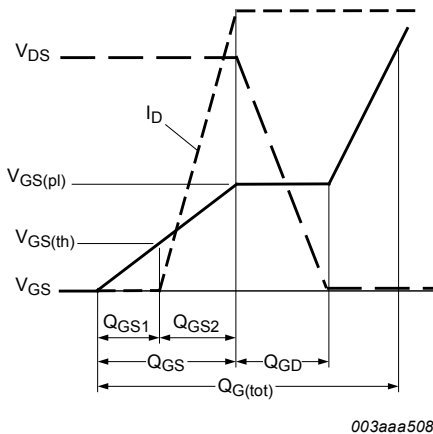


Fig. 14. Gate charge waveform definitions

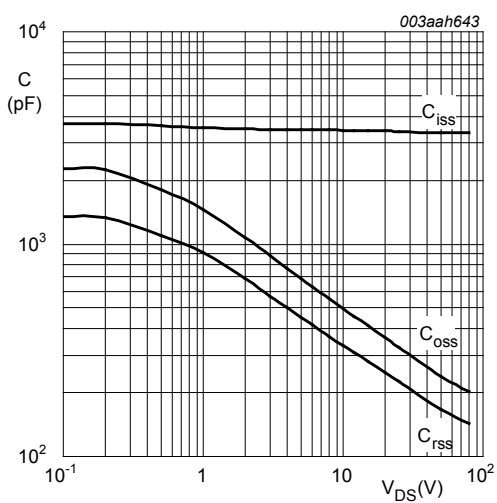


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0\text{ V}; f = 1\text{ MHz}$$

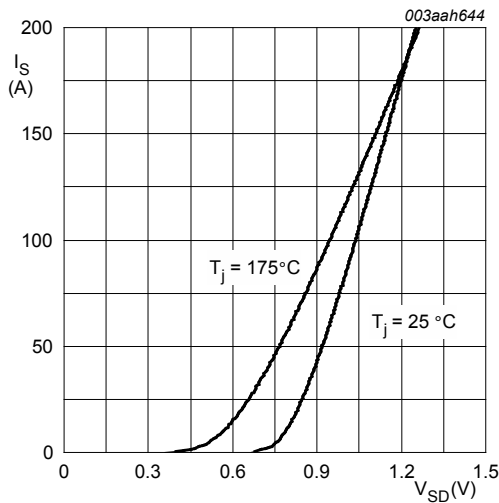


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values

$V_{GS} = 0V$

8. Package outline

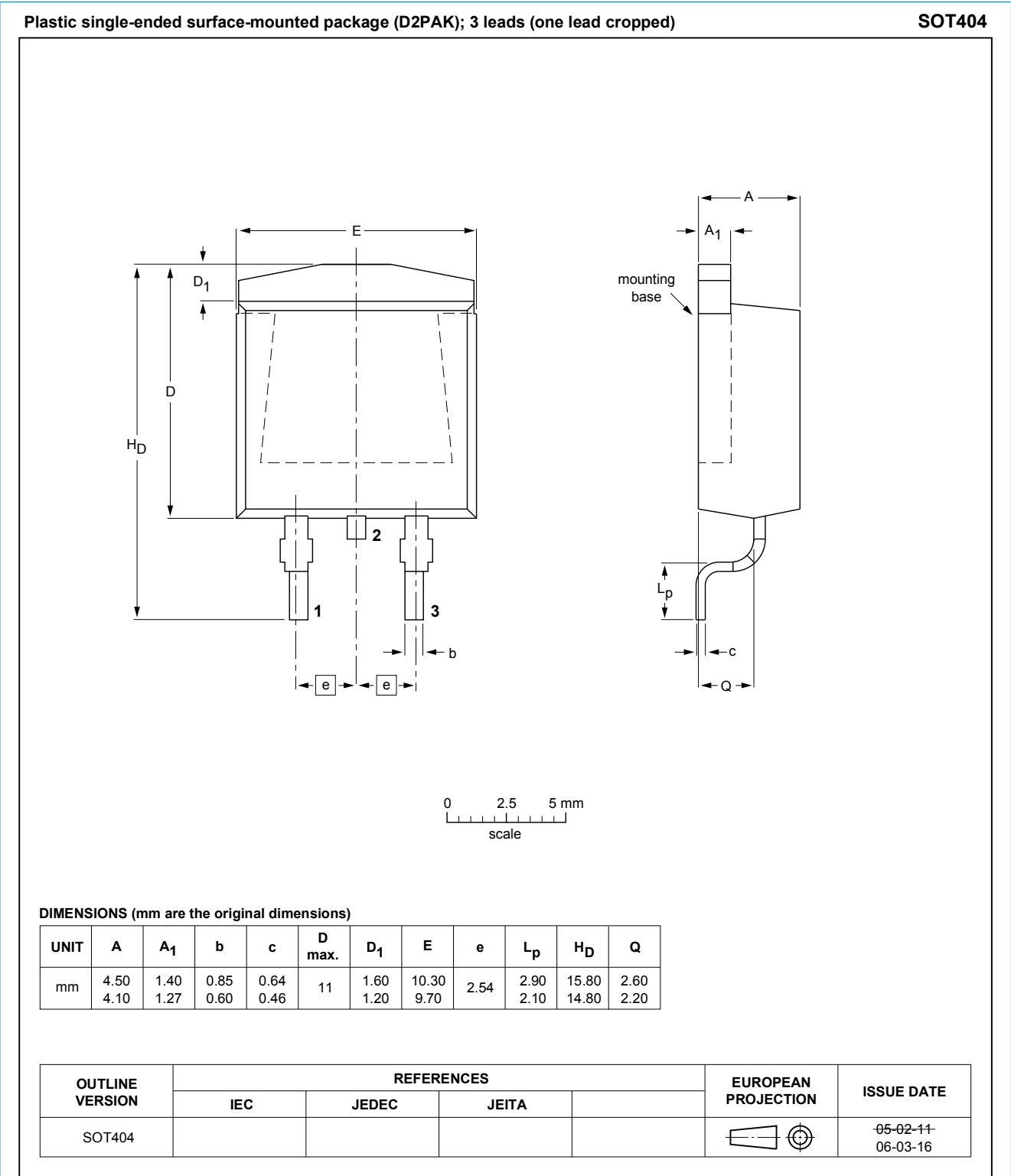


Fig. 17. Package outline D2PAK (SOT404)

9. Legal information

9.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
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10. Contents

1 Product profile 1

1.1 General description 1

1.2 Features and benefits1

1.3 Applications 1

1.4 Quick reference data 1

2 Pinning information2

3 Ordering information2

4 Marking 2

5 Limiting values2

6 Thermal characteristics4

7 Characteristics 5

8 Package outline 10

9 Legal information11

9.1 Data sheet status 11

9.2 Definitions 11

9.3 Disclaimers 11

9.4 Trademarks 12

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